

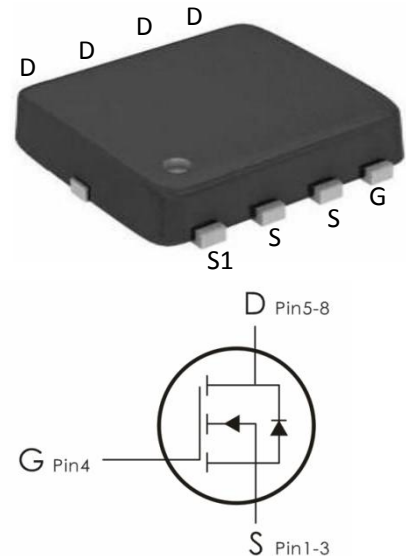
Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=30V, I_D=80A, R_{DS(on)} < 3.5\text{ m}\Omega @ V_{GS}=10V$ (Typ : $2.9\text{ m}\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DOZ80N03	80N03	DFN3*3-8	5000 pcs/Reel

Absolute Maximum Ratings: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	80	A
	Continuous Drain Current- $T_C=100^\circ\text{C}$	55	
I_{DM}	Pulsed Drain Current ¹	240	
P_D	Power Dissipation	49	W
E_{AS}	Single pulse avalanche energy ²	121	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.55	$^\circ\text{C}/\text{W}$

R_{θJA}	Thermal Resistance, Junction to Ambient ³	41	°C/W
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Electrical Characteristics: (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	30	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =30V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	1.3	1.9	2.5	V
R _{DS(ON)}	Drain-Source On Resistance ⁴	V _{GS} =10V, I _D =30A	---	2.9	3.5	m Ω
		V _{GS} =4.5V, I _D =20A	---	4.6	6	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	3088	---	pF
C _{oss}	Output Capacitance		---	371	--	
C _{rss}	Reverse Transfer Capacitance		---	301	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =15V, I _D =30A, R _G =3 Ω ,V _{GS} =10V	---	10	---	ns
t _r	Rise Time		---	28	---	ns
t _{d(off)}	Turn-Off Delay Time		---	46	---	ns
t _f	Fall Time		---	17	---	ns
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =30A	---	57	---	nC
Q _{gs}	Gate-Source Charge		---	11	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	12	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage ¹	V _{GS} =0V, I _{SD} =30A	---	---	1.2	V
I _S	Continuous Drain Curren ³	V _D =V _G =0V	---	---	80	A
I _{SM}	Pulsed Drain Current		---	---	240	A
T _{rr}	Reverse Recovery Time	I _F =30A, T _J =25 °C	---	16	---	NS

Qrr	Reverse Recovery Charge	di/dt=100A/us	---	7	---	NC
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Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. EAS condition: Starting $T_J=25^\circ\text{C}$, $V_{DD}=15\text{V}$, $V_G=10\text{V}$, $R_G=25\Omega$, $L=0.5\text{mH}$, $I_{AS}=22\text{A}$
3. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB
4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Typical Characteristics: ($T_C=25^\circ\text{C}$ unless otherwise noted)

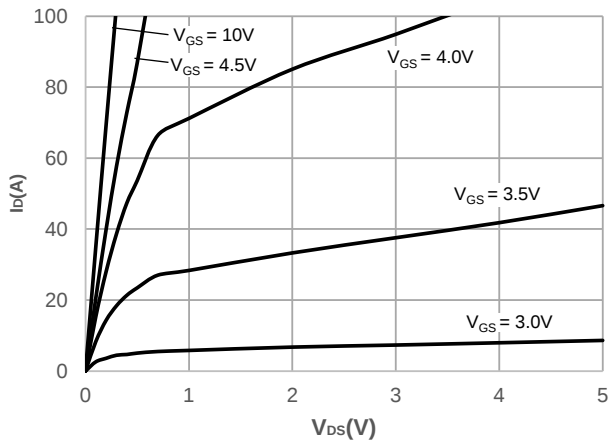


Figure 1: Output Characteristics

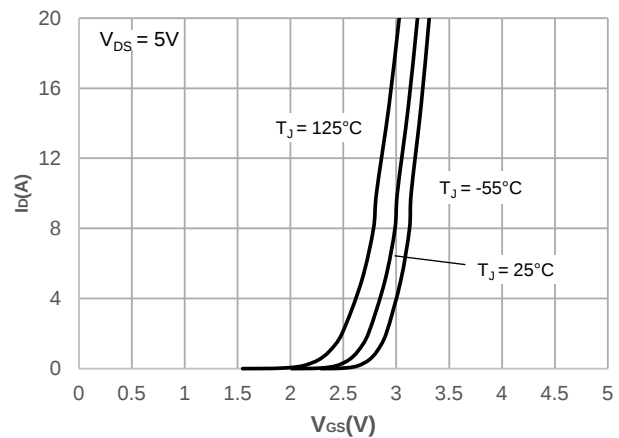


Figure 2: Typical Transfer Characteristics

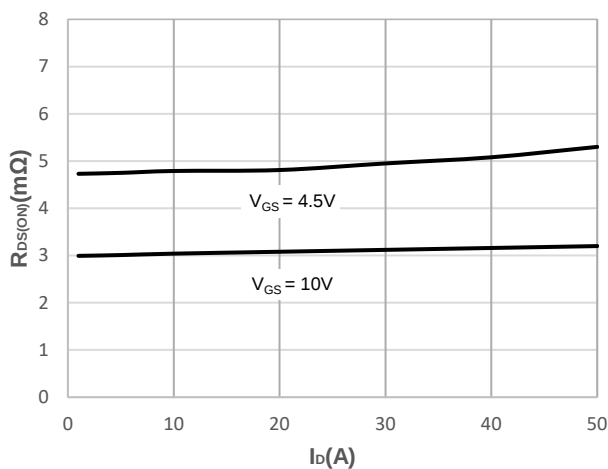


Figure 3: On-resistance vs. Drain Current

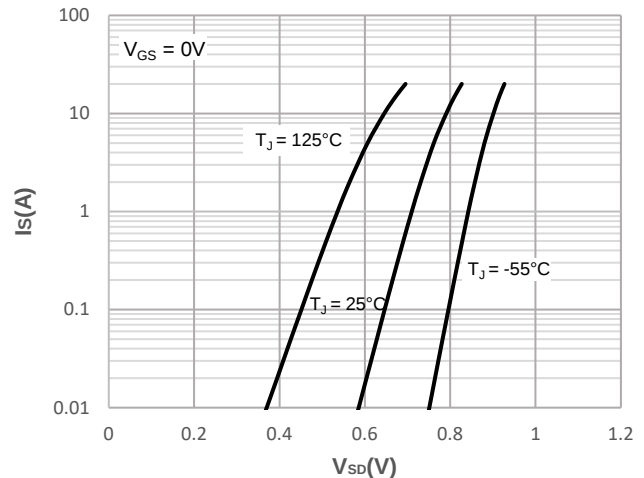


Figure 4: Body Diode Characteristics

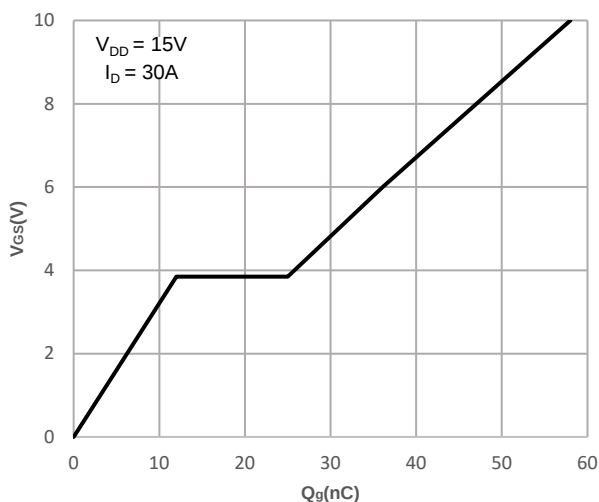


Figure 5: Gate Charge Characteristics

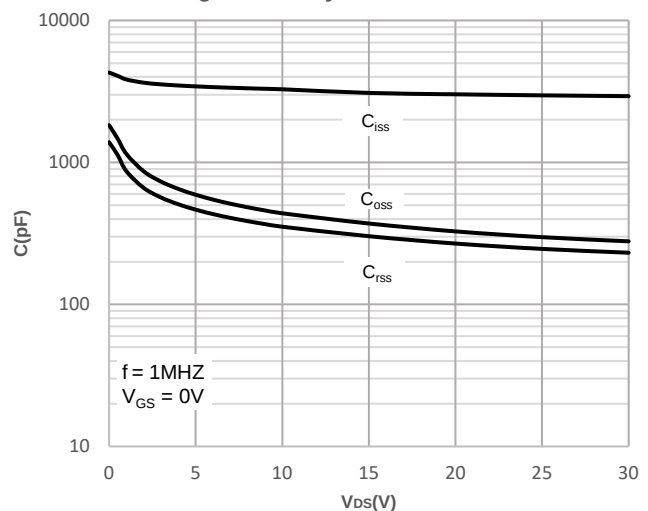


Figure 6: Capacitance Characteristics

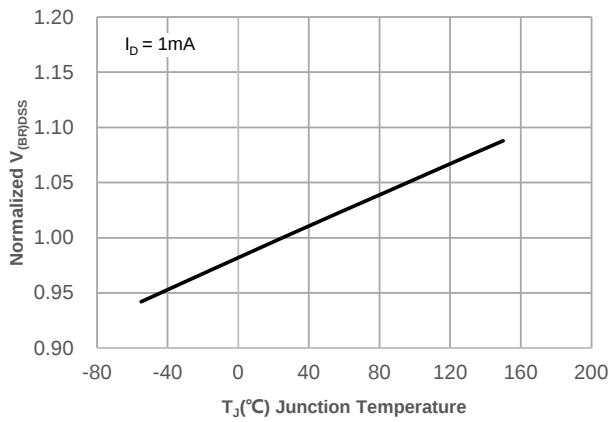


Figure 7: Normalized Breakdown voltage vs. Junction Temperature

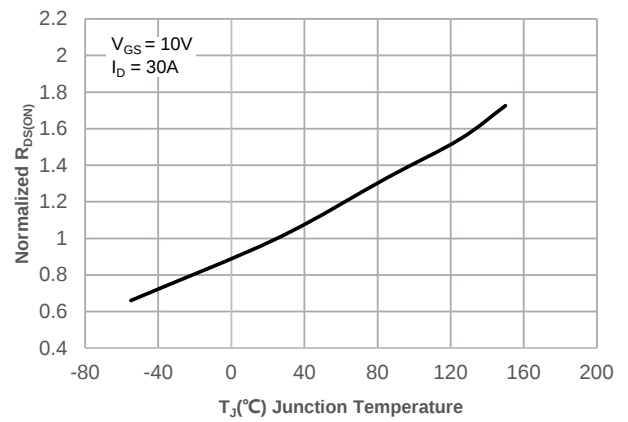


Figure 8: Normalized on Resistance vs. Junction Temperature

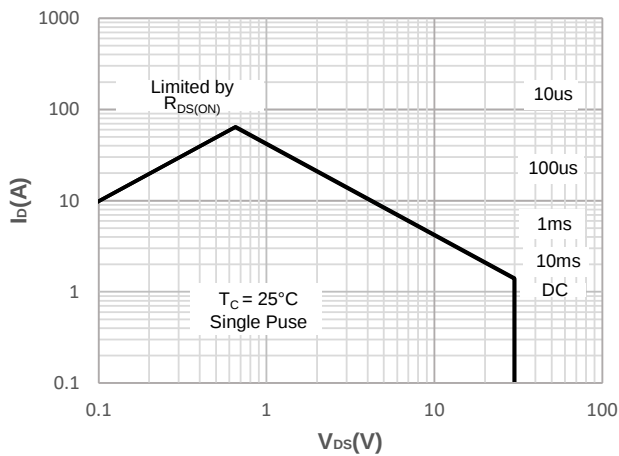


Figure 9: Maximum Safe Operating Area

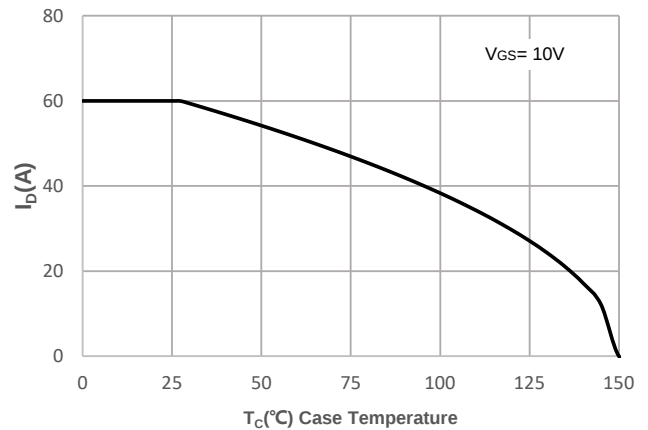


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

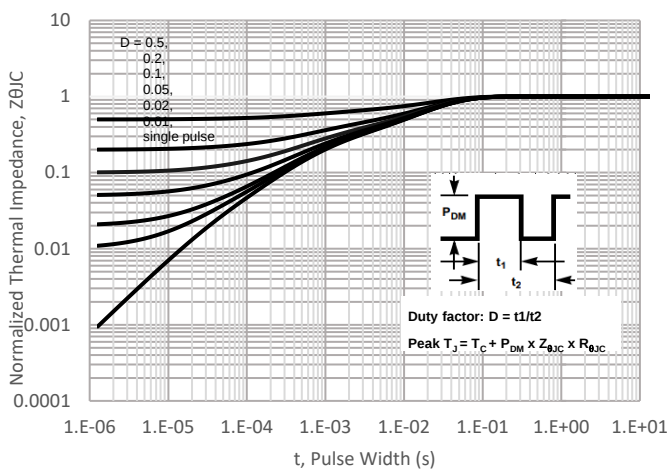


Figure 11: Normalized Maximum Transient Thermal Impedance

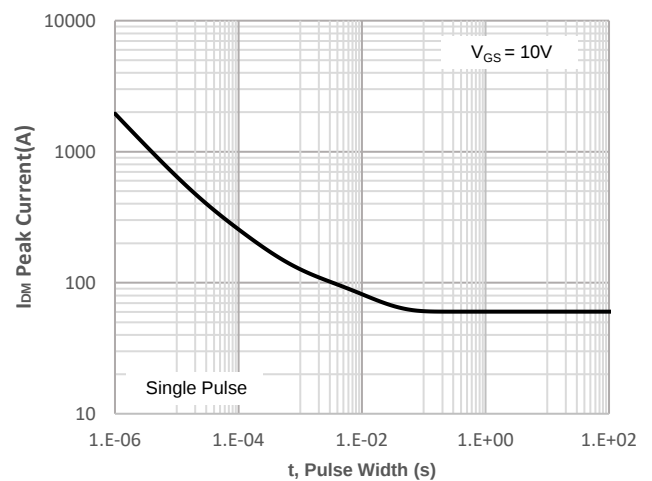
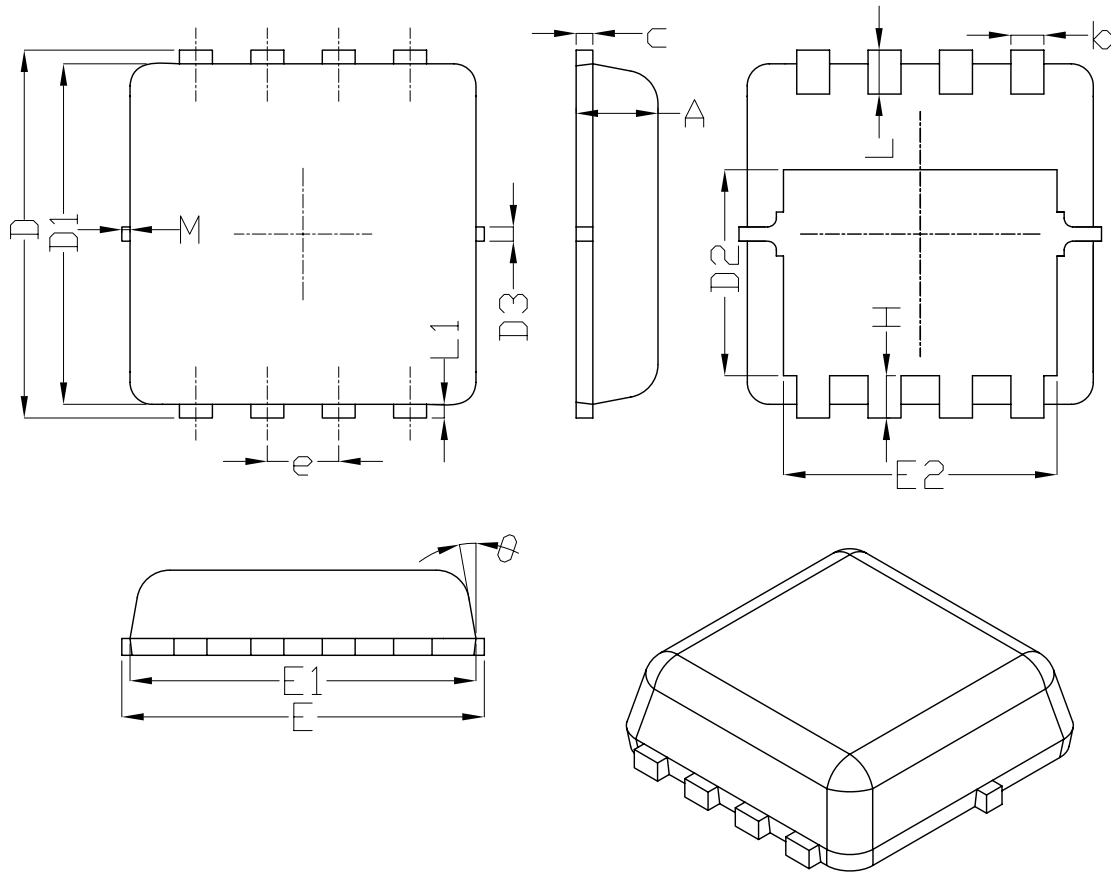
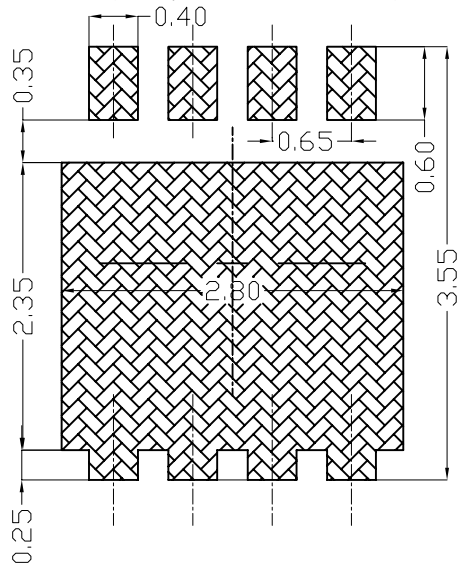


Figure 12: Peak Current Capacity

DFN3X3-8Package Outline Data


**Land Pattern
(Only for Reference)**



UNIT: mm

SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	---	0.13	---
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	---	0.13	---
θ	---	10°	12°
M	*	*	0.15

* Not specified

Package Information:

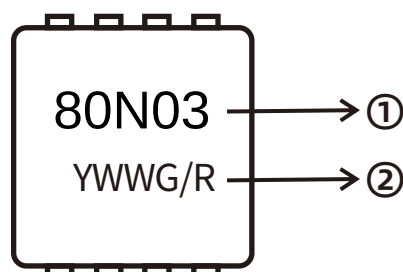
①. Part NO.

②. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)



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